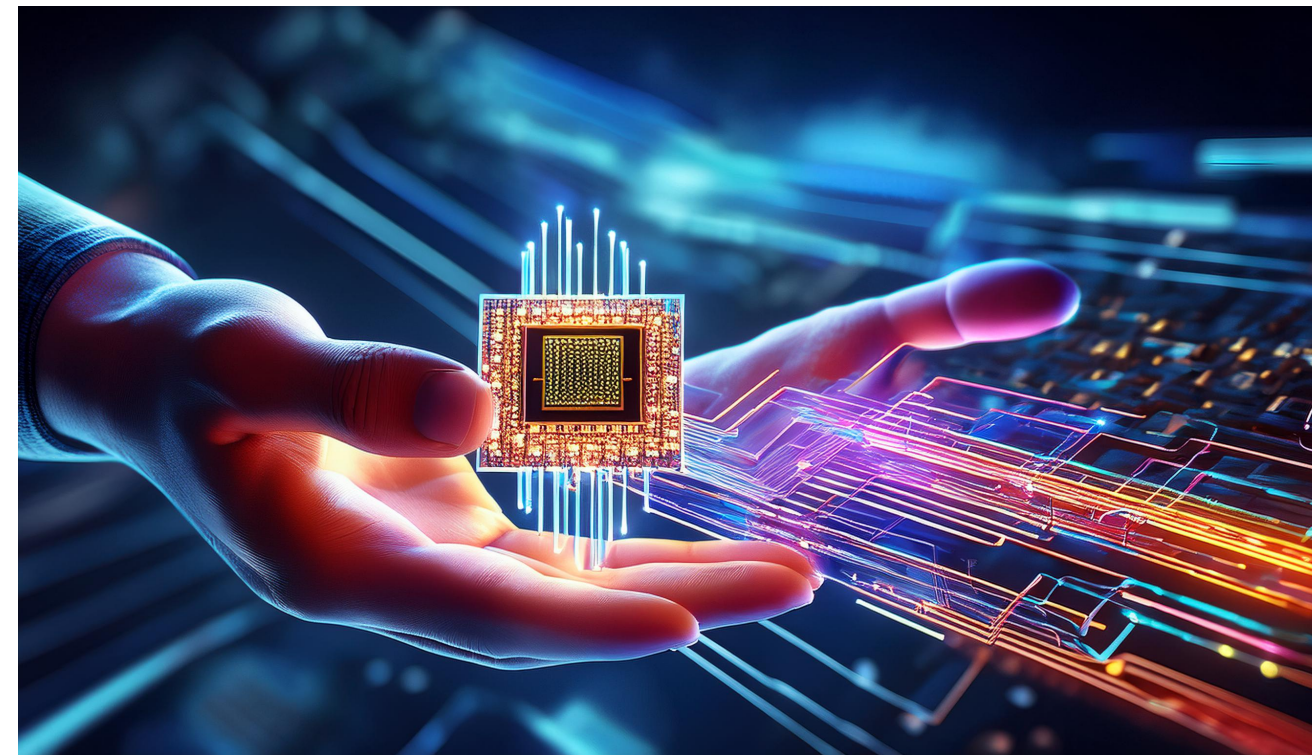




# CSCI 250

## Introduction to Computer Organisation

### Lecture 2: Computer Memory II



Jetic Gū

# Overview

- Focus: Course Introduction
- Architecture: Logical Circuits
- Textbook: v4: 8.3; v5: 7.3
- Core Ideas:
  1. RAM in FPGA
  2. Building RAM Modules
  3. Lab 2

# RAM in Verilog

# RAM Modules

- Two primary types of memory for FPGA:
  - On-die (On-chip): the amount of memory located on the FPGA chip. Often SRAM
  - Onboard: the amount of memory available to the chip, but located on the board. Often DDR RAM
- On-die RAM modules are automatically synthesised and created in Verilog. This will be our focus today
- Onboard RAM chips vary depending on manufacturer and model

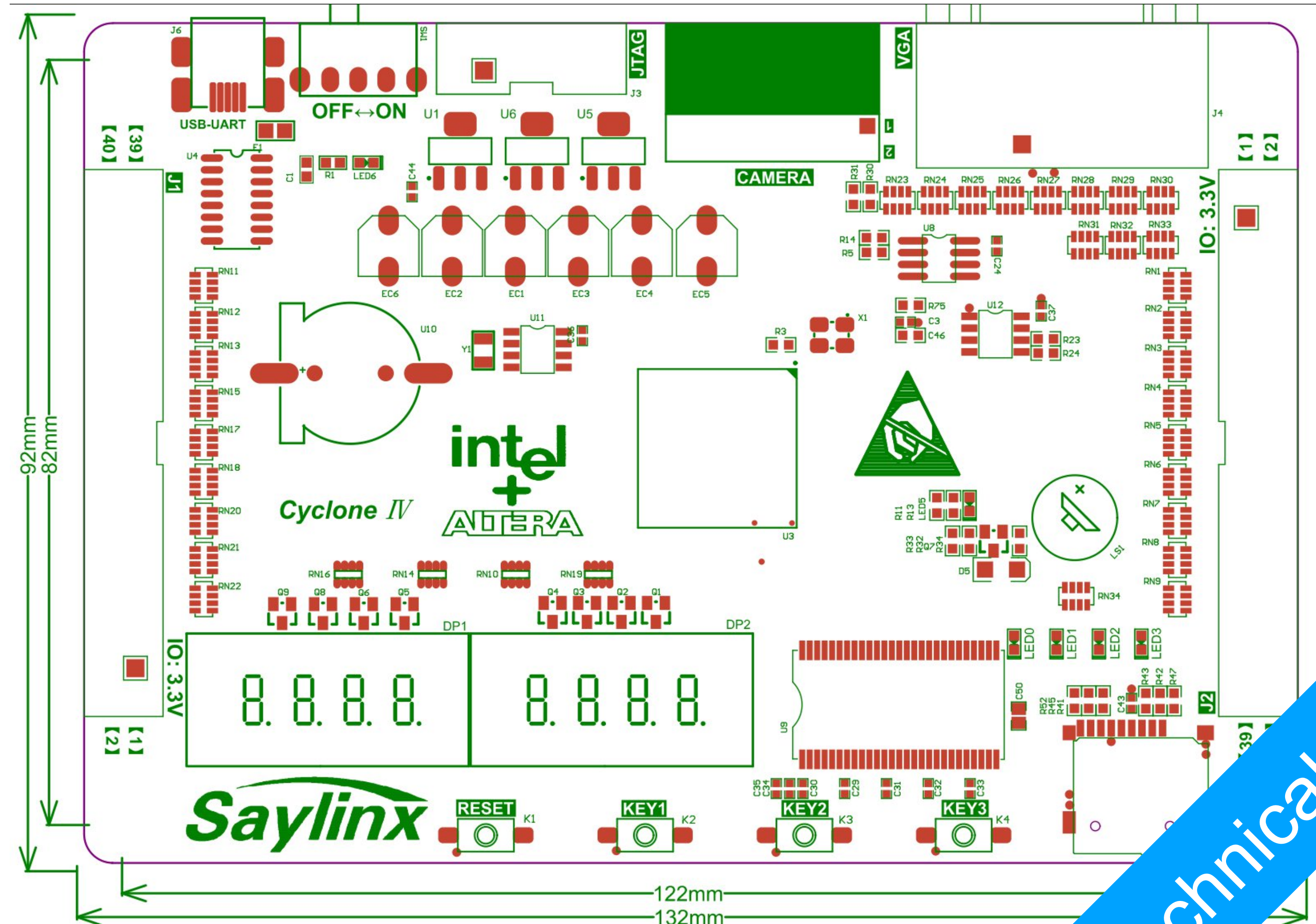
# RAM Modules

- For example: my board (PIAX301-V2 dev board, using Cyclone IV EP4CE6F17I7)
- On-die: 270 Kbit. These cover all of the registers, flip-flops, latches, etc. If you want on-die SRAM, this is also what they use.
- Onboard: 256 Mbit. These are dynamic RAM, and the chip is external to the FPGA die. They have their own interfaces



# RAM Modules

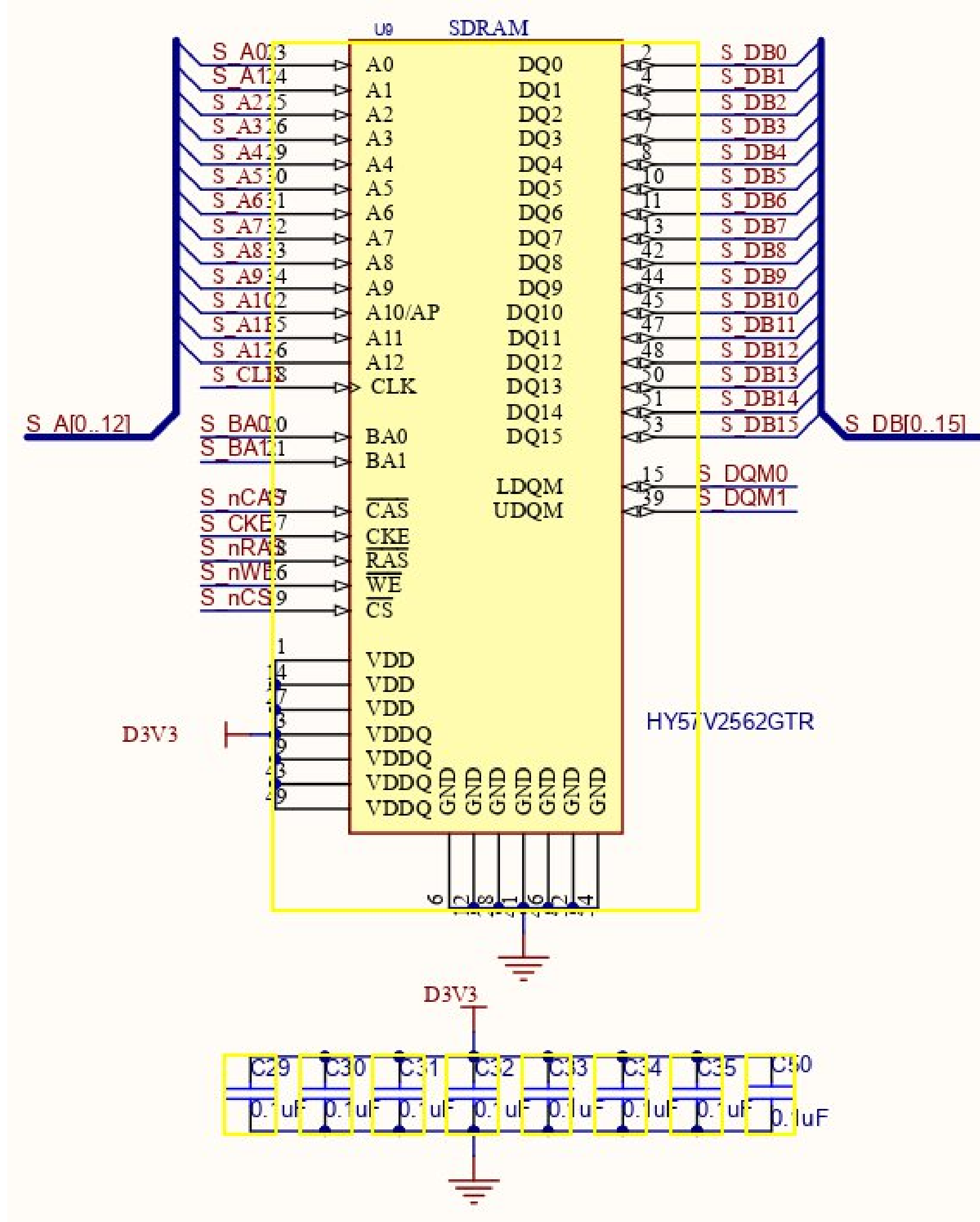
- This is my board, this is taken from the dev manual of my board
- You can see the names of each pin of each IO on this board



Technical

# RAM Modules

- This is my onboard DSRAM
- 16bits for data, bi-directional
- 13bits for address, these go out from the FPGA chip into the DSRAM module



sdram_we_n	Unknown	PIN_J13
sdram_ras_n	Unknown	PIN_K11
sdram_dqm[0]	Unknown	PIN_J14
sdram_dqm[1]	Unknown	PIN_G15
sdram_dq[0]	Unknown	PIN_P14
sdram_dq[1]	Unknown	PIN_M12
sdram_dq[2]	Unknown	PIN_N14
sdram_dq[3]	Unknown	PIN_L12
sdram_dq[4]	Unknown	PIN_L13
sdram_dq[5]	Unknown	PIN_L14
sdram_dq[6]	Unknown	PIN_L11
sdram_dq[7]	Unknown	PIN_K12
sdram_dq[8]	Unknown	PIN_G16
sdram_dq[9]	Unknown	PIN_J11
sdram_dq[10]	Unknown	PIN_J16
sdram_dq[11]	Unknown	PIN_J15
sdram_dq[12]	Unknown	PIN_K16
sdram_dq[13]	Unknown	PIN_K15
sdram_dq[14]	Unknown	PIN_L16
sdram_dq[15]	Unknown	PIN_L15
sdram_cs_n	Unknown	PIN_K10
sdram_clk	Unknown	PIN_B14
sdram_cke	Unknown	PIN_F16
sdram_cas_n	Unknown	PIN_J12
sdram_ba[0]	Unknown	PIN_G11
sdram_ba[1]	Unknown	PIN_F13
sdram_addr[0]	Unknown	PIN_F11
sdram_addr[1]	Unknown	PIN_E11
sdram_addr[2]	Unknown	PIN_D14
sdram_addr[3]	Unknown	PIN_C14
sdram_addr[4]	Unknown	PIN_A14
sdram_addr[5]	Unknown	PIN_A15
sdram_addr[6]	Unknown	PIN_B16
sdram_addr[7]	Unknown	PIN_C15
sdram_addr[8]	Unknown	PIN_C16
sdram_addr[9]	Unknown	PIN_D15
sdram_addr[10]	Unknown	PIN_F14
sdram_addr[11]	Unknown	PIN_D16
sdram_addr[12]	Unknown	PIN_F15

# Building RAM Modules

# Why On-Die RAM

- We need to simulate having a RAM chip
  - We will setup a synchronous sequential module with the same interface as our example SDRAM onboard chip
  - During simulation, we use this on-die RAM module
- Should we use on-die RAM modules or onboard RAM modules in production?

# Code for RAM Module

- Single-port RAM: means we have one databus for both read and write, and one address bus
- Basic Interfaces:
  - $A[12:0]$ : for memory address
  - $DB[15:0]$ : for databus
  - $clk$ : Clock,  $oe$ : Output Enabled,  $we$ : Write Enabled,  $cs$ : Chip Select;

# Code for RAM Module

- #: **parameters** are like constants you declare as macros in C/C++. They are replaced by actual values at compile time
- Width: number of bits
- Depth here: number of unique memory addresses
- Note: this is **NOT** byte-addressable memory
- Real byte-addressable memory requires more steering to enable individual byte read/write. Not necessary to us

```
module ram
# (parameter ADDR_WIDTH = 13,
  parameter DATA_WIDTH = 16,
  parameter DEPTH = 8192
)

(  input          clk,
  input [ADDR_WIDTH-1:0]  a,
  inout [DATA_WIDTH-1:0] db,
  input          cs,
  input          we,
  input          oe
);

reg [DATA_WIDTH-1:0] tmp_data;
reg [DATA_WIDTH-1:0] mem [DEPTH:0];

always @ (posedge clk) begin
  if (cs & we)
    mem[a] <= db;
end

always @ (posedge clk) begin
  if (cs & !we)
    tmp_data <= mem[a];
end

assign db= cs & oe & !we ? tmp_data : 'hz;
endmodule
```

# Code for RAM Module

- inout: bidirectional wire here, nothing to see

cs ChipSelect	we WriteEnable	oe OutputEnable	Behaviour
0	X	X	Output 'hZ, high-Z
1	0	0	Read mode No output
1	0	1	Read mode Output db
1	1	0	Write mode No output
1	1	1	Write mode No output

```

module ram
  # (parameter ADDR_WIDTH = 13,
    parameter DATA_WIDTH = 16,
    parameter DEPTH = 8192
  )

  (  input          clk,
    input [ADDR_WIDTH-1:0] a,
    inout [DATA_WIDTH-1:0] db,
    input          cs,
    input          we,
    input          oe
  );

  reg [DATA_WIDTH-1:0] tmp_data;
  reg [DATA_WIDTH-1:0] mem [DEPTH:0];

  always @ (posedge clk) begin
    if (cs & we)
      mem[a] <= db;
  end

  always @ (posedge clk) begin
    if (cs & !we)
      tmp_data <= mem[a];
  end

  assign db = cs & oe & !we ? tmp_data : 'hZ;
endmodule

```

# Code for RAM Module

- mem: main memory array
  - Brackets before: the contents for each address, 16bits
  - Brackets after: the number of words in the memory, 8192 words
- tmp\_data: temporary buffer for data to go out
  - Think: why not go directly out?

```
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  )

  (  input          clk,
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    inout [DATA_WIDTH-1:0] db,
    input          cs,
    input          we,
    input          oe
  );

  reg [DATA_WIDTH-1:0] tmp_data;
  reg [DATA_WIDTH-1:0] mem [DEPTH:0];

  always @ (posedge clk) begin
    if (cs & we)
      mem[a] <= db;
    end

  always @ (posedge clk) begin
    if (cs & !we)
      tmp_data <= mem[a];
    end

  assign db = cs & oe & !we ? tmp_data : 'hz;
endmodule
```

# Code for RAM Module

- always: procedural block
  - Statements inside an always block are executed sequentially
- @ (posedge clk): trigger
  - This block is executed at the **positive edge** of CLK
- If just one statement, no need for begin/end

```
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# (parameter ADDR_WIDTH = 13,
  parameter DATA_WIDTH = 16,
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)

(  input          clk,
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  inout [DATA_WIDTH-1:0] db,
  input          cs,
  input          we,
  input          oe
);

reg [DATA_WIDTH-1:0] tmp_data;
reg [DATA_WIDTH-1:0] mem [DEPTH:0];

always @ (posedge clk) begin
  if (cs & we)
    mem[a] <= db;
end

always @ (posedge clk) begin
  if (cs & !we)
    tmp_data <= mem[a];
end

assign db = cs & oe & !we ? tmp_data : 'hz;
endmodule
```

# Code for RAM Module

- Is this sequential or combinational?
- `expr ? exprA : exprB`
- This is called a Ternary Operator, same as in C/C++
- Difference? This is combinational
- You can write it as boolean operators only (How?)

```
module ram
# (parameter ADDR_WIDTH = 13,
  parameter DATA_WIDTH = 16,
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)
(
  input          clk,
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  if (cs & !we)
    tmp_data <= mem[a];
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assign db = cs & oe & !we ? tmp_data : 'hz;
endmodule
```

# Building RAM Modules

# What will you need to build?

- A Python Exercise (See LS7)
- An SRAM Cell using block diagram (See LS5)
- A RAM module using Verilog (LS6), with DQM (more to follow)<sup>1</sup>
- Waveform simulation required

<sup>1</sup>.<https://www.alldatasheet.com/datasheet-pdf/view/333572/HYNIX/H57V2562GTR-75C.html>